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TITLE: SEMICONDUCTOR DEVICE AND ITS MANUFACTURE

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APPL-NO: JP09215025

APPL-DATE: August 8, 1997

US-CL-CURRENT: 257/E29.259

INT-CL (IPC): H01 L 29/78

ABSTRACT:

PROBLEM TO BE SOLVED: To omit a necessary photo-mask process by forming recessed parts on the drain layer of an area excepting the forming areas of gate electrodes and sidewalls and forming a wiring layer so that channel layers exposed from the recessed parts, the sidewalls and insulating films are coated.

SOLUTION: The channel layers 23 are formed on an n-type epitaxial layer 22. Then, an n+ type impurity diffusion layer is formed on the surface with the gate insulating films 25 and gate electrodes 26 as masks. Thus, sidewalls 28 are formed on the sidewalls of the gate insulating films 25, the gate electrodes 26 and the insulating films 27. A part of the channel layers 23 is etched and the recessed parts are formed. The n+ type impurity diffusion layer is cut by the recessed parts and source area layers 24 are formed at the same time. Then, P+ type body contacts 23A are formed by implanting borons, a metallic film is formed on the whole face and it is patterned.

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PATENT FAMILY INFORMATION

AN 110608181 INPADOC

+-----PRAI-----+	+-----AI-----+
JP 1997-215025 A 19970808	JP 1997-215025 A 19970808
+-----AI-----+	+-----PI-----+
JP 1997-215025 A 19970808	JP 11068093 A2 19990309
	JP 3326366B B2 20020924

1 priority, 1 application, 2 publications

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